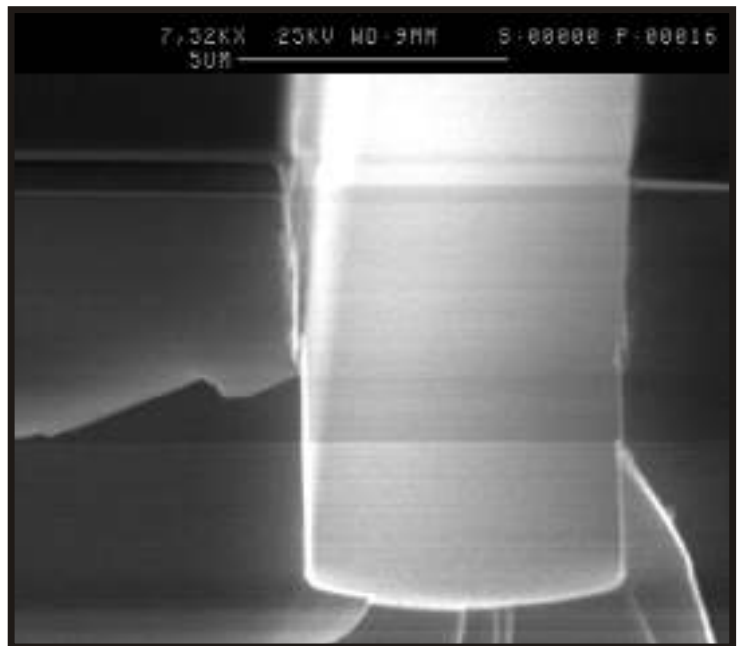
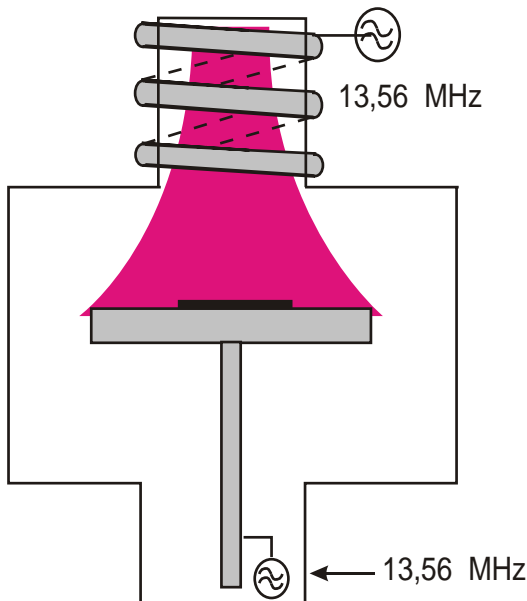


Plasmalab Data

GaSb ICP Etching



- Plasmalab 80 Plus*
- Plasmalab System 100*
- Plasmalab System 133*

OPT application lab:
7 µm deep GaSb etch, Cl₂ based

Technology:

Reactive Ion Etching
with ICP Source (2 or 13 MHz)
Inductive Coupled Plasma
RF driven substrate electrode

Results:

Rate : 2 µm/ min
selectivity to SiO₂ mask 25 : 1
good uniformity
smooth surface
anisotropic profile

